



STTH3003CW

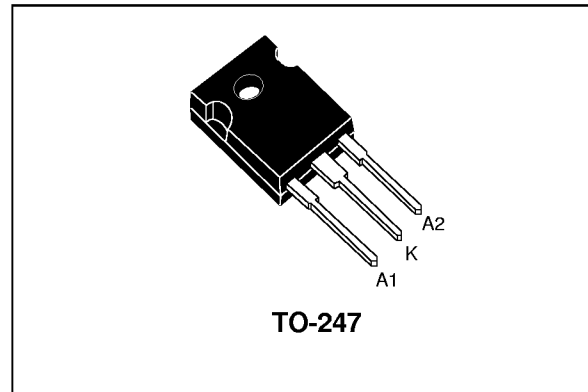
HIGH FREQUENCY SECONDARY RECTIFIER

MAJOR PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 15 A
V_{RRM}	300 V
T_j (max)	175 °C
V_F (max)	1 V
t_{rr} (max)	40 ns

FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND REVERSE VOLTAGE PERFORMANCE
- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY



DESCRIPTION

Dual center tap Fast Recovery Epitaxial Diodes suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-247 this device is intended for secondary rectification.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		300	V
$I_{F(RMS)}$	RMS forward current		30	A
$I_{F(AV)}$	Average forward current	$T_c = 135^\circ\text{C}$ $\delta = 0.5$	Per diode 30 Per device	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10$ ms sinusoidal	140	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 20$ μs square	7	A
T_{stg}	Storage temperature range		-65 +175	°C
T_j	Maximum operating junction temperature		+175	°C

STTH3003CW

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	2.0
		Total	1.05
$R_{th(c)}$	Coupling	0.1	

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = 300\text{ V}$	$T_j = 25^\circ\text{C}$		40	μA
			$T_j = 125^\circ\text{C}$		400	
V_F^{**}	Forward voltage drop	$I_F = 15\text{ A}$	$T_j = 25^\circ\text{C}$		1.25	V
			$T_j = 125^\circ\text{C}$		0.85	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.75 \times I_{F(AV)} + 0.017 I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Tests conditions	Min.	Typ.	Max.	Unit
t_{rr}	$I_F = 0.5\text{ A}$ $I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$			30	ns
	$I_F = 1\text{ A}$ $dl_F/dt = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$			40	
t_{fr}	$I_F = 15\text{ A}$ $dl_F/dt = 100\text{ A}/\mu\text{s}$			300	ns
V_{FP}	$V_{FR} = 1.1 \times V_F \text{ max.}$			3.5	V
S_{factor}	$V_{CC} = 200\text{ V}$ $I_F = 15\text{ A}$		0.3		-
I_{RM}	$dl_F/dt = 200\text{ A}/\mu\text{s}$			8.5	A

Fig. 1: Conduction losses versus average current (per diode).

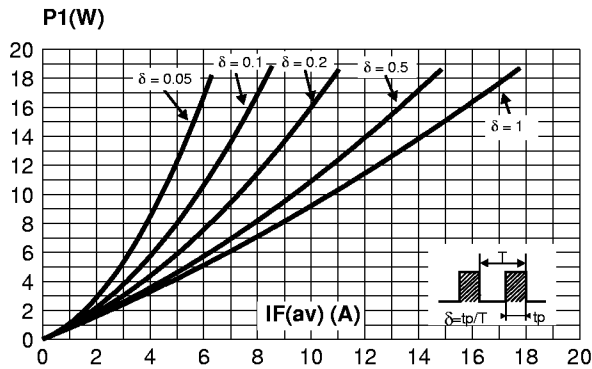


Fig. 2: Forward voltage drop versus forward current (maximum values, per diode).

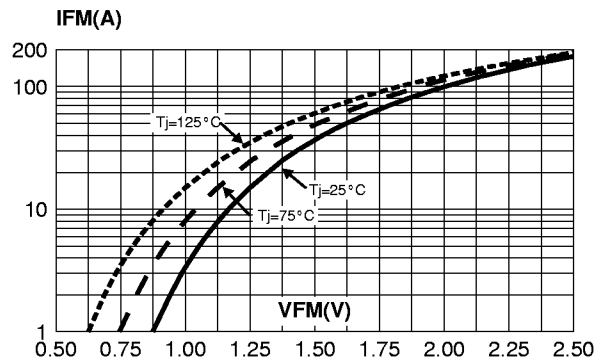


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

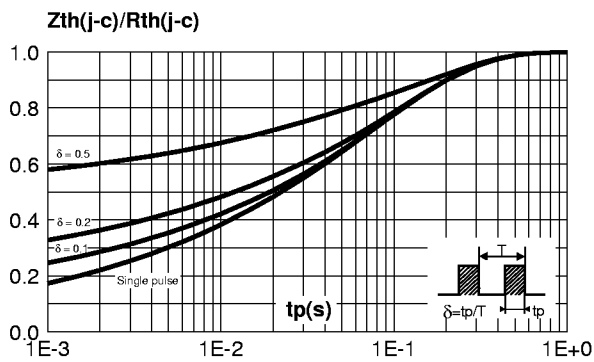


Fig. 4: Peak reverse recovery current versus dI/dt (90% confidence, per diode).

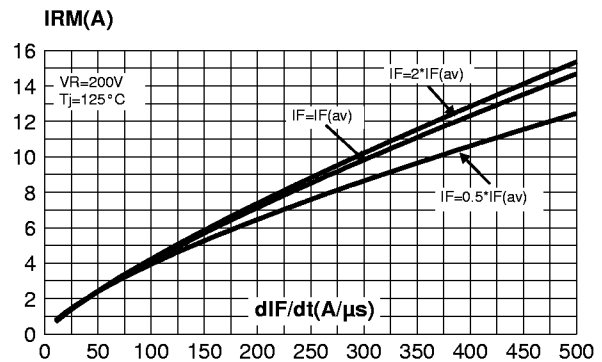


Fig. 5: Reverse recovery time versus dI/dt (90% confidence, per diode).

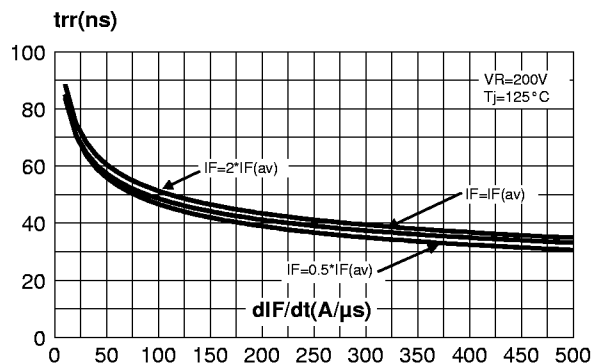
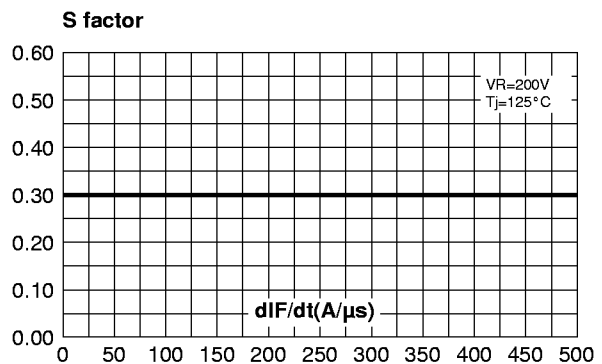


Fig. 6: Softness factor versus dI/dt (typical values, per diode).



STTH3003CW

Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference: $T_j = 125^\circ\text{C}$).

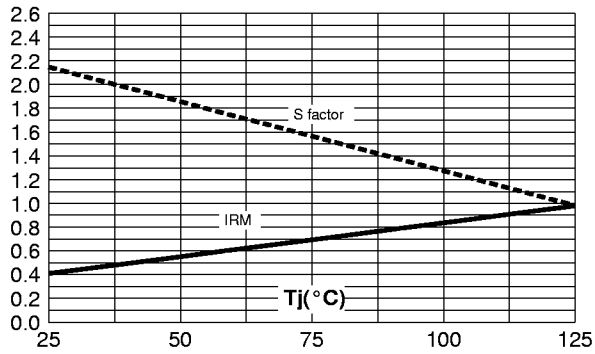


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence, per diode).

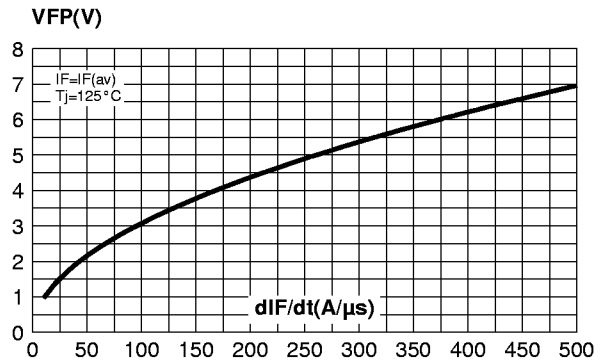
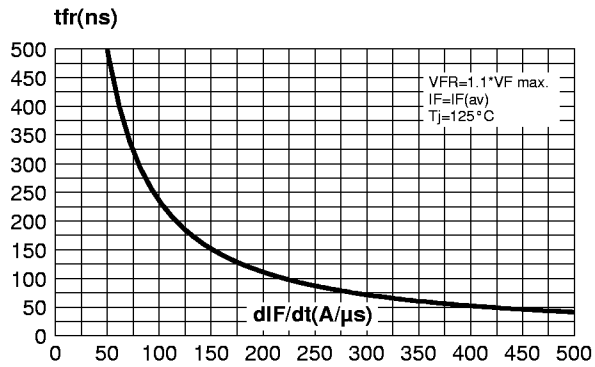
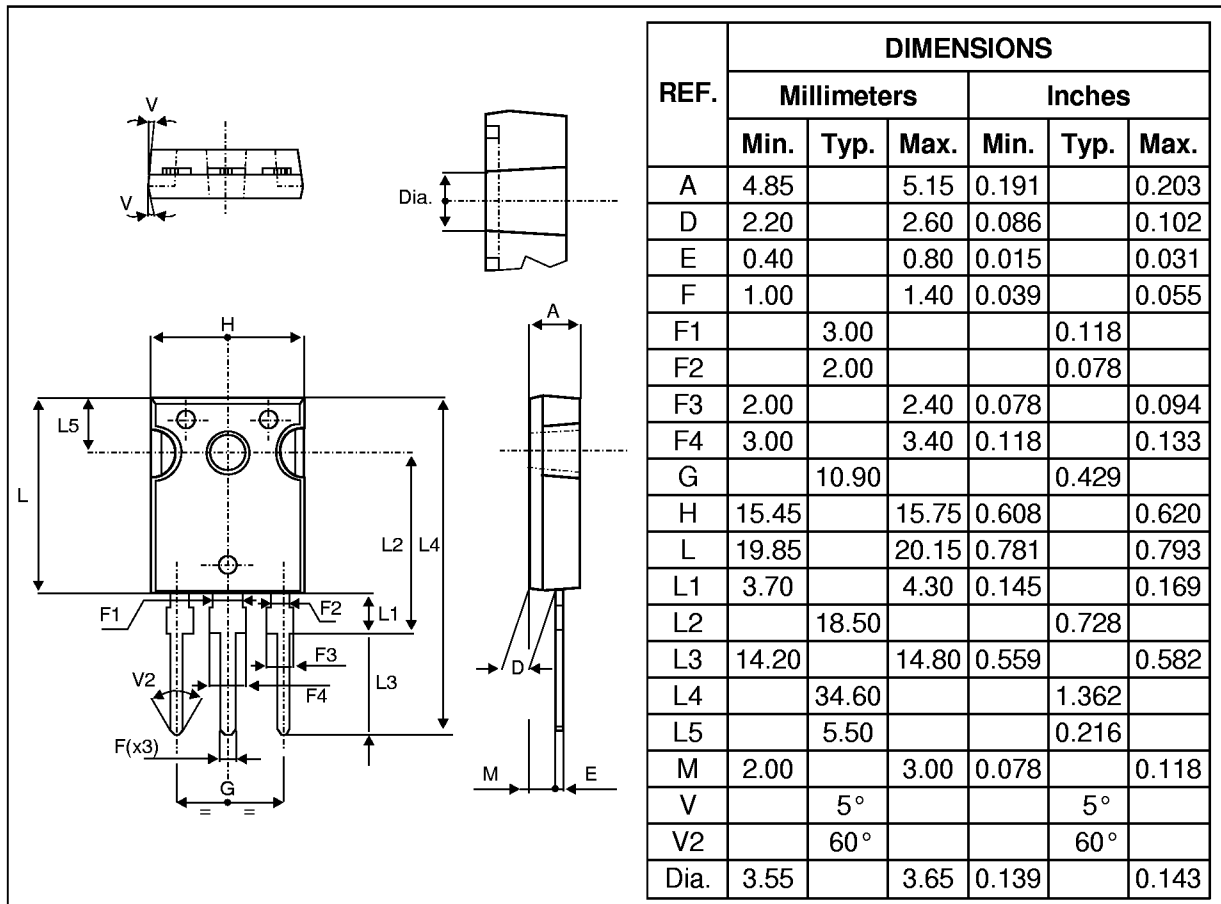


Fig. 9: Forward recovery time versus dI_F/dt (90% confidence, per diode).



PACKAGE MECHANICAL DATA
 TO-247


Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH3003CW	STTH3003CW	TO-247	4.36g	30	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1.0 N.m.
- Epoxy meets UL 94,V0

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 1999 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia
 Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>

